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(Use Several Sheets if Necessary)	Filing Date March 17, 2004	Group Not Yet Assigned 1763

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
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	B	4,413,022	11/1/83	Suntola et al			
	C	4,798,165	1/17/89	deBoer et al			
	D	5,006,363	4/9/91	Fujii et al			
	E	5,294,568	3/15/94	McNeilly et al			
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	H	5,773,078	6/30/98	Skelly			
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Foreign Patent or Published Foreign Patent Application

Foreign Patent or Published Foreign Patent Application								
Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub- class	Translation	
							Yes	No
	PP							

Other Documents

Other Documents

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MGA	RR	Laun et al, Ultra Thin High Quality Ta2O5 Gate Dielectric Prepared By In Situ Rapid Thermal Processing, 1999, Tech Dig Int Electron Device Meet, 4 Pages
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MGA	VV	Schuiskey et al, Atomic Layer Chemical Vapor Deposition of TiO2 Low Temperature Epitaxy of Rutile and Anatase, 2000, Journal of The Electrochemical Society, Vol 147(9), pp 3319-3325
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MGA	YY	Higashi et al, Sequential Surface Chemical Reaction Limited Growth of High Quality Al2O3 dielectrics
Examiner		Date Considered
/Maureen Arancibia/		01/19/2007

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.